

Test progress INFN

Solution 1

~~Opening time ≤ 1 ms seems feasible, with replacement of the MOSFET's, introduction of a series resistance, new protections against extra voltage, re-calibration and test is feasible in a few months.~~

Is the discharge through 24 diodes + 8 m Ω is acceptable for the protection point of view (max 100 V)?

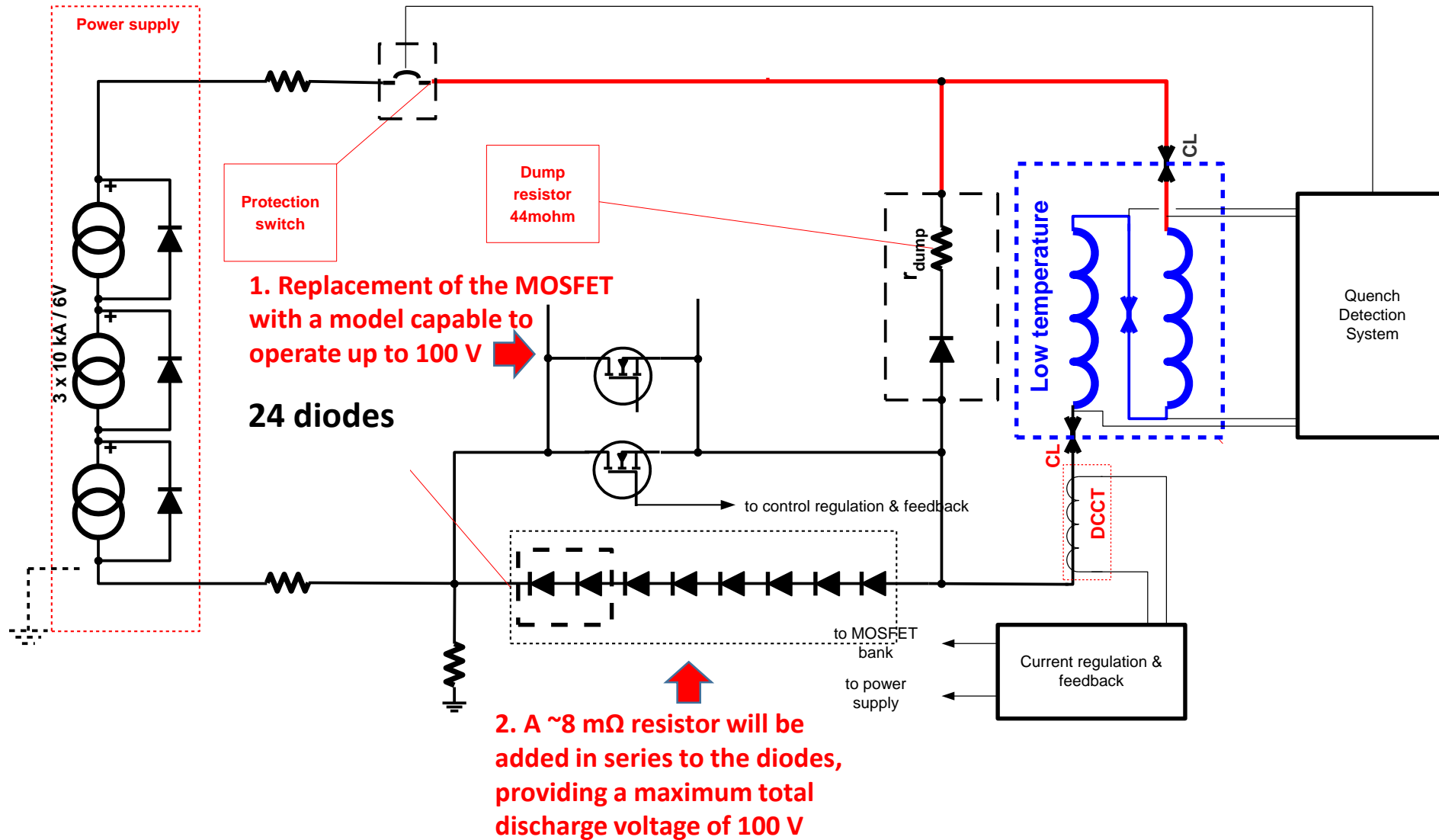
Let's say larger than 100 V...

Solution 2

Replacement of the MOSFET's with modules based on IGBT, which can sustain higher voltages. In this case there is a max voltage drop about 400 V (limited by the test station) This requires an extensive redesign of the discharge unit, with new heat exchanger, current connection, control electronics... etc., so unlikely in time for the end of the next year.

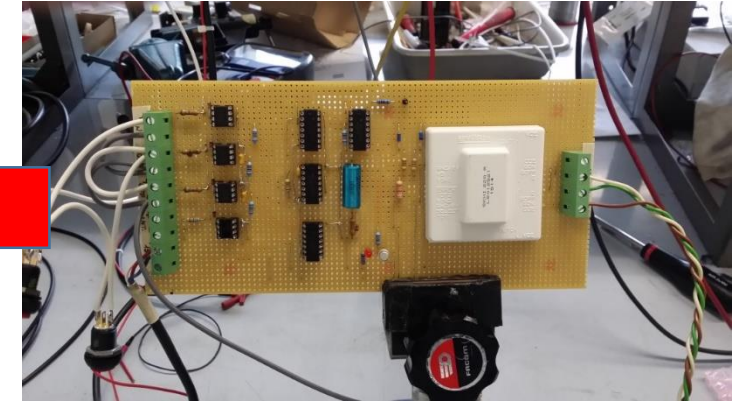
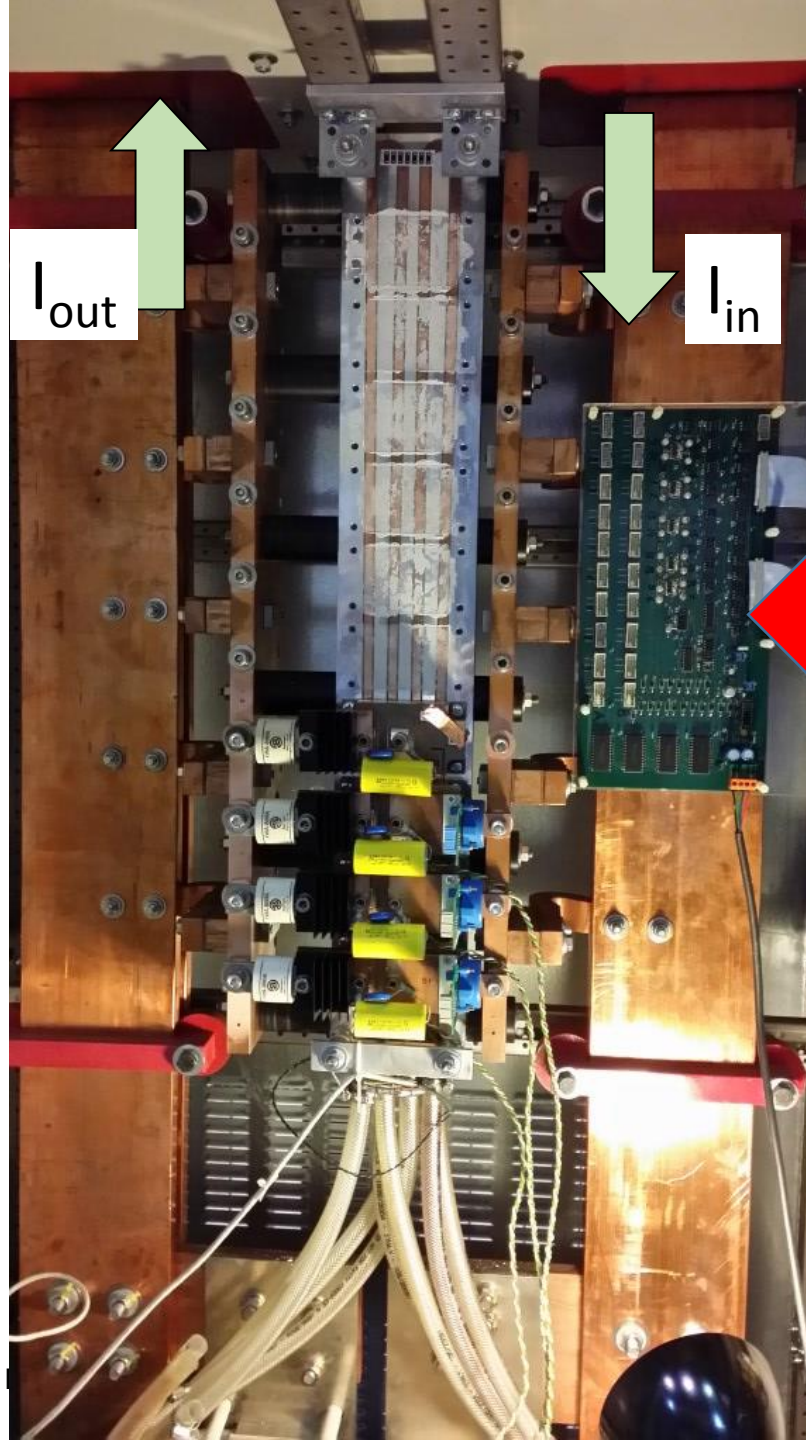
Solution 3

Another Fast / Solid State Switch?



MOSFET's replaced by IGBT 's which are more suitable thanks to their higher V_{CEmax}
Their V_{on} is however larger, and the extra dissipation will be disposed of through a larger water flow within the heat exchanger.

Test in progress with four IGBT's in parallel, if OK more elements, up to 20, will be installed



New control board based on a hybrid IGBT driver circuit

MAGIX cryostat is not the best choice:

- Too short
- Less room in the top flange

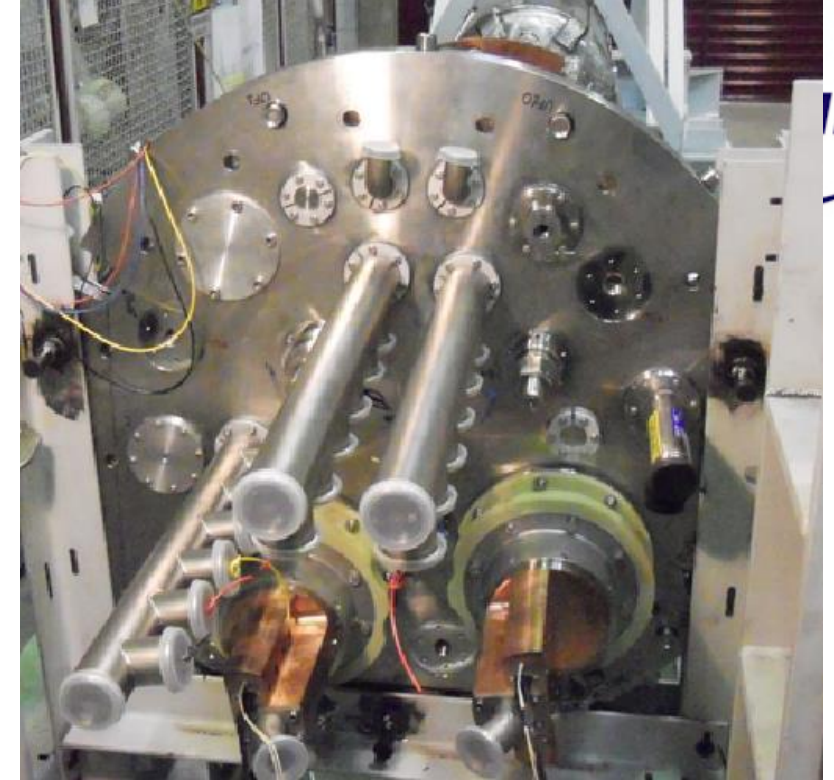
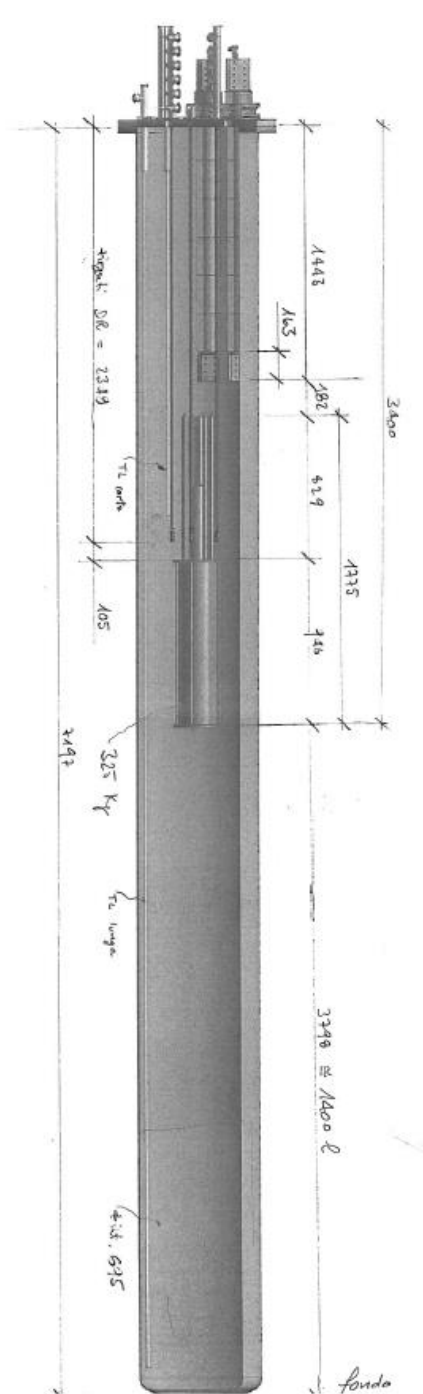
So we switched to the larger DISCORAP cryostat

- All equipment (top flange, radiation shield, tie rods) available

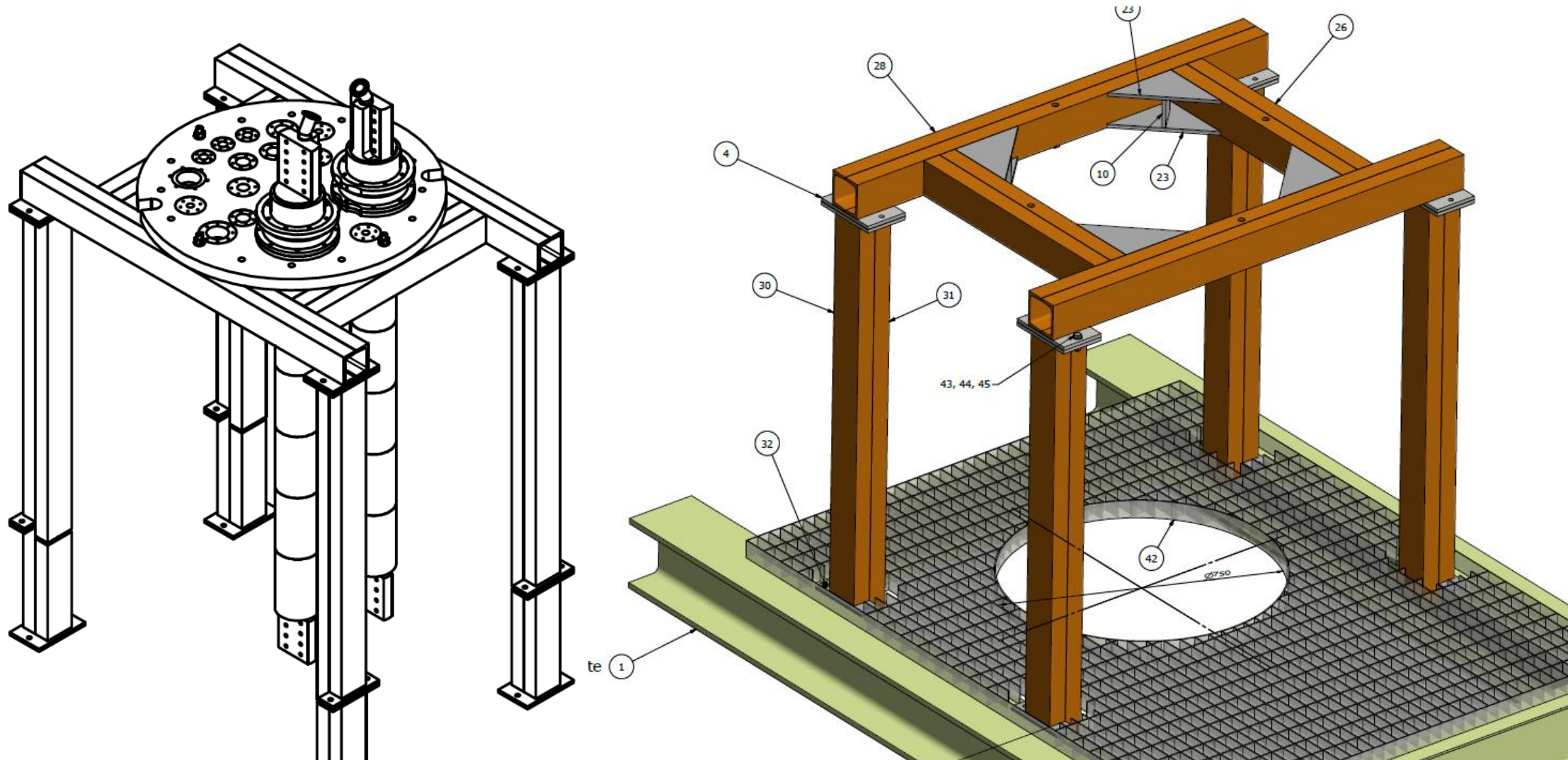
Lower cryostat

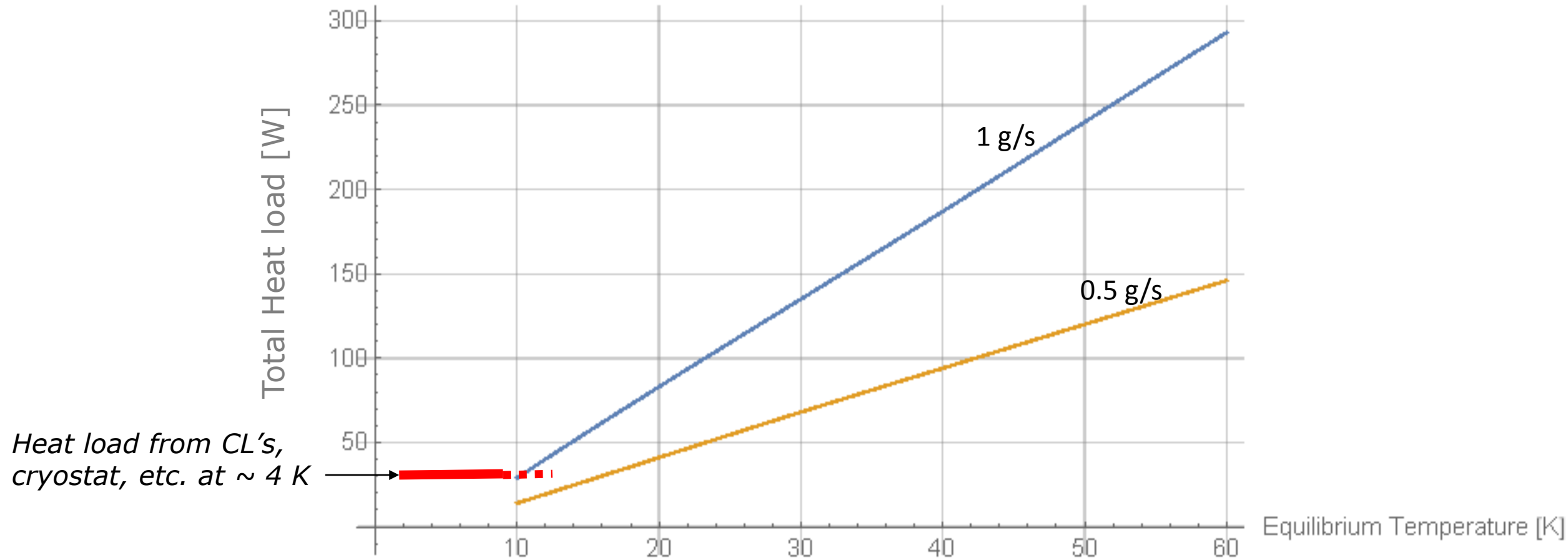
(1.4 m³) filled with PlastazoteTM, whose density is close to LHe.

Not suitable for LN test



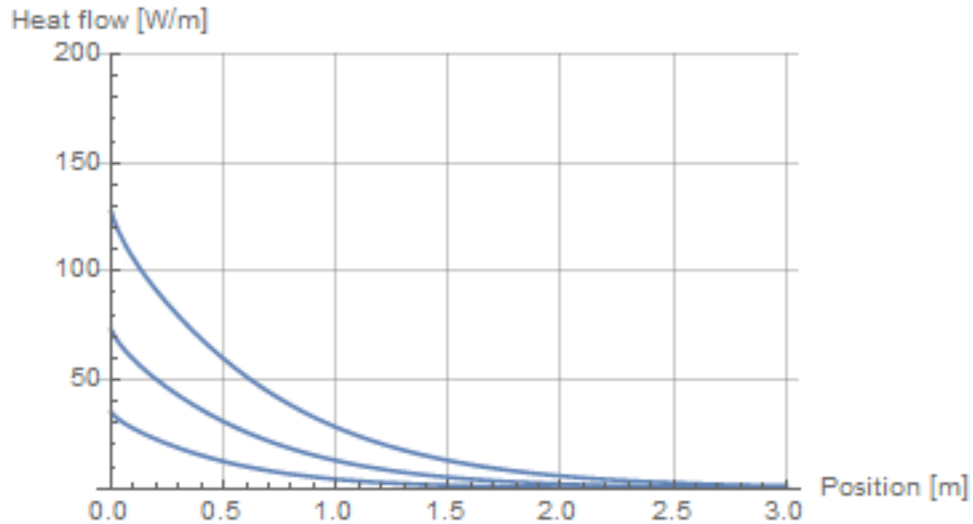
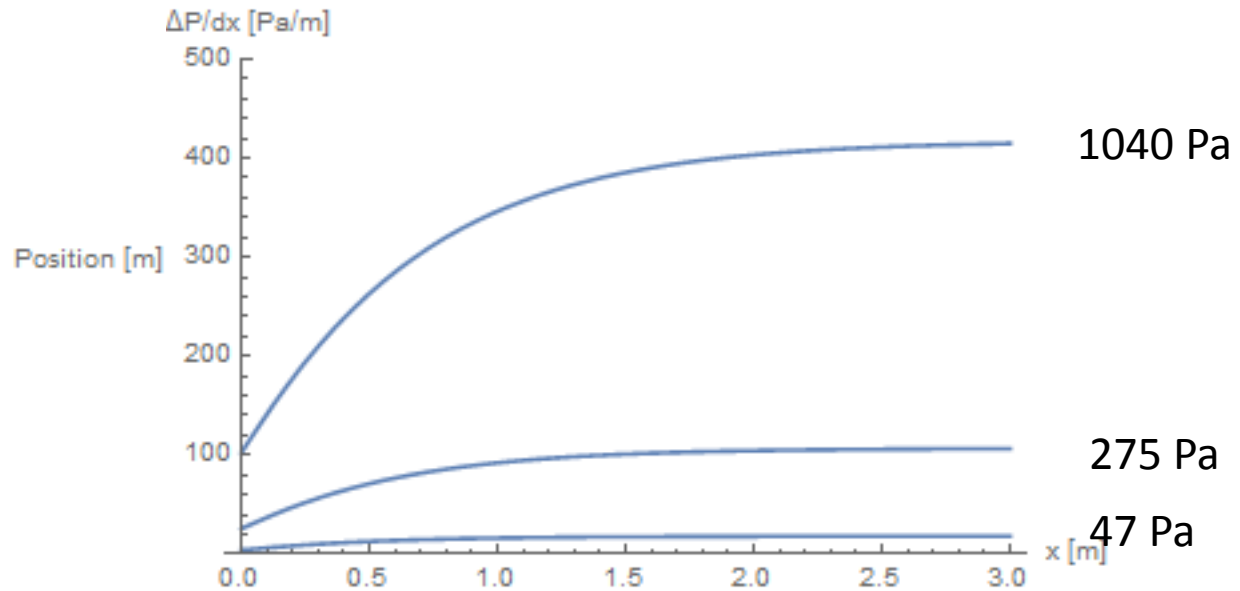
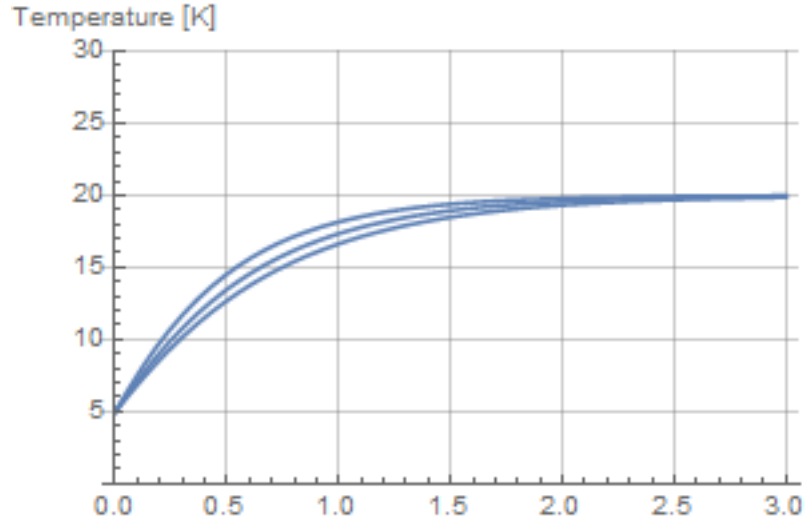
Assembly station: may be accessed from ground floor and lower floor





T = 20 K

0.2, 0.5, 1.0 g/s



$T = 60 \text{ K}$

0.2, 0.5, 1.0 g/s

